

## NXPS20H100C Dual power Schottky diode Rev. 2 — 8 June 2012

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a SOT78 (TO-220AB) plastic package.

### **1.2 Features and benefits**

- High junction temperature capability
- Low leakage current

### Negligible switching losses

Optimised design to give low V<sub>F</sub> and high T<sub>i(max)</sub>

### **1.3 Applications**

- DC to DC converters
- Freewheeling diode

- OR-ing diode
- Switched mode power supply rectifier

### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	100	V
I <sub>F(AV)</sub>	average forward current	square-wave pulse; $\delta = 0.5$ ; T <sub>mb</sub> ≤ 163 °C; per diode; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	10	A
I <sub>O(AV)</sub>	average output current	square-wave pulse; $\delta = 0.5$ ; T <sub>mb</sub> ≤ 161 °C; both diodes conducting	-	-	20	А
Tj	junction temperature		-	-	175	°C
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; see <u>Figure 6</u>	-	-	0.77	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; see <u>Figure 6</u>	-	0.59	0.64	V
I <sub>R</sub>	reverse current	$V_R$ = 100 V; $T_j$ = 25 °C; see <u>Figure 7</u>	-	2	4.5	μA
		V <sub>R</sub> = 100 V; T <sub>i</sub> = 125 °C; see Figure 7	-	1	6	mA

# 

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode	mb	
3	A2	anode 2		К
mb	К	mounting base; cathode		sym125

SOT78 (TO-220AB)

### 3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
NXPS20H100C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

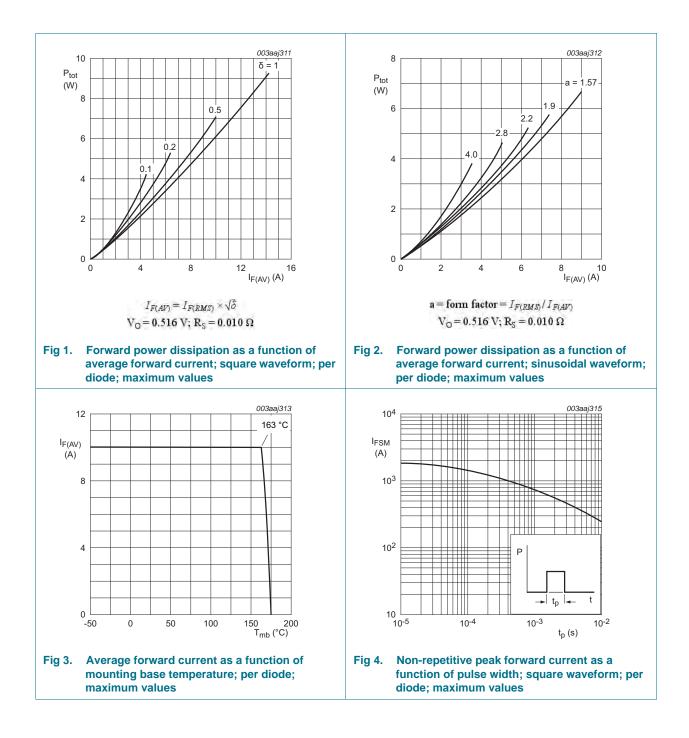
### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

-				
Parameter	Conditions	Min	Max	Unit
repetitive peak reverse voltage		-	100	V
average forward current	square-wave pulse; $\delta = 0.5$ ; T <sub>mb</sub> ≤ 163 °C; per diode; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	10	A
average output current	square-wave pulse; $\delta = 0.5$ ; T <sub>mb</sub> ≤ 161 °C; both diodes conducting	-	20	А
non-repetitive peak forward current	sine-wave pulse; t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; see <u>Figure 4</u>	-	250	A
storage temperature		-65	175	°C
junction temperature		-	175	°C
	repetitive peak reverse voltage average forward current average output current non-repetitive peak forward current storage temperature	repetitive peak reverse voltageaverage forward currentsquare-wave pulse; $\delta = 0.5$ ; $T_{mb} \leq 163 °C$ ; per diode; see Figure 1; see Figure 2; see Figure 3average output currentsquare-wave pulse; $\delta = 0.5$ ; $T_{mb} \leq 161 °C$ ; both diodes conductingnon-repetitive peak forward currentsine-wave pulse; $t_p = 10 ms$ ; $T_{j(init)} = 25 °C$ ; see Figure 4storage temperature	repetitive peak reverse voltage-average forward currentsquare-wave pulse; $\delta = 0.5$ ; $T_{mb} \leq 163 ^{\circ}$ C; per diode; see Figure 1; see Figure 2; see Figure 3-average output currentsquare-wave pulse; $\delta = 0.5$ ; $T_{mb} \leq 161 ^{\circ}$ C; both diodes conducting-non-repetitive peak forward currentsine-wave pulse; $t_p = 10 \text{ms}$ ; $T_{j(init)} = 25 ^{\circ}$ C; see Figure 4-storage temperature-65	repetitive peak reverse voltage-100average forward currentsquare-wave pulse; $\delta = 0.5$ ; $T_{mb} \leq 163 ^{\circ}$ C; per diode; see Figure 1; see Figure 2; see Figure 3-10average output currentsquare-wave pulse; $\delta = 0.5$ ; $T_{mb} \leq 161 ^{\circ}$ C; both diodes conducting-20non-repetitive peak forward currentsine-wave pulse; $t_p = 10 \text{ms}$ ; $T_{j(init)} = 25 ^{\circ}$ C; see Figure 4-250storage temperature-65175

#### **Dual power Schottky diode**

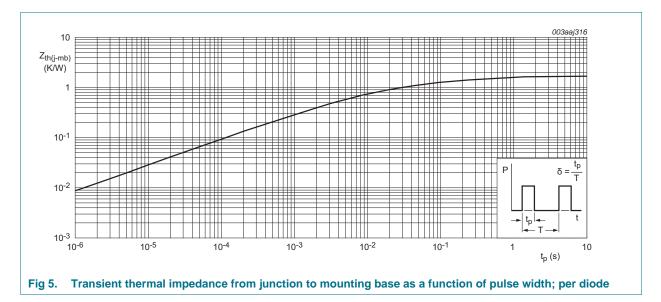


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### 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; see <u>Figure 5</u>	-	-	1.6	K/W
		with heatsink compound; both diodes conducting	-	-	0.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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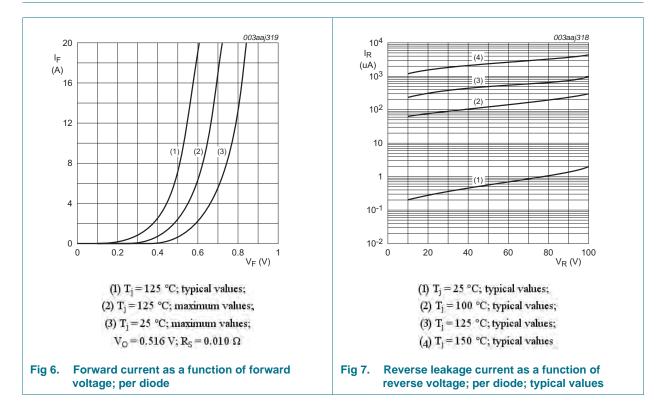
**Dual power Schottky diode** 

#### **Characteristics** 6.

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; see <u>Figure 6</u>	-	-	0.71	V
		$I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{1000 \text{ G}}$	-	-	0.77	V
		I <sub>F</sub> = 16 A; T <sub>j</sub> = 25 °C; see <u>Figure 6</u>	-	-	0.81	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; see <u>Figure 6</u>	-	-	0.88	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; see <u>Figure 6</u>	-	0.56	0.58	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; see <u>Figure 6</u>	-	0.59	0.64	V
		I <sub>F</sub> = 16 A; T <sub>j</sub> = 125 °C; see <u>Figure 6</u>	-	0.65	0.68	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; see <u>Figure 6</u>	-	0.67	0.73	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C; see <u>Figure 7</u>	-	2	4.5	μA
		$V_R = 100 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{Figure 7}}$	-	1	6	mA
Dynamic	characteristics					
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C;	-	250	-	pF

diode capacitance

f = 1 MHz; V<sub>R</sub> = 10 V; T<sub>i</sub> = 25 °C; see Figure 8

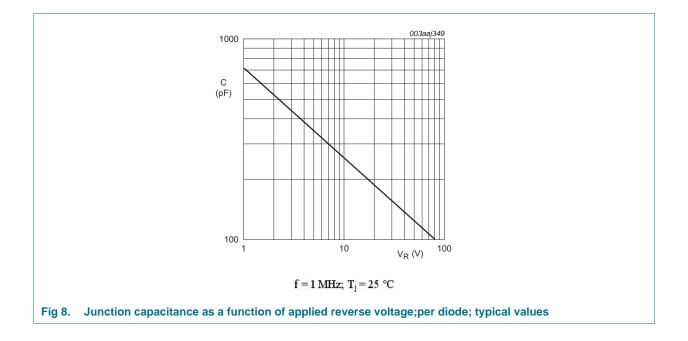


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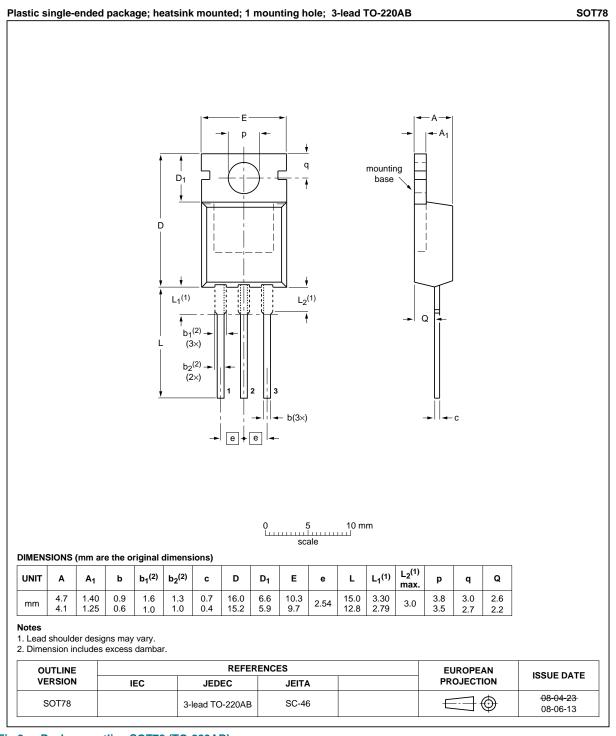
#### **Dual power Schottky diode**





**Dual power Schottky diode** 

### 7. Package outline



### Fig 9. Package outline SOT78 (TO-220AB)

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### 8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
NXPS20H100C v.2	20120608	Product data sheet	-	NXPS20H100C v.1
Modifications:	<ul> <li>Status change</li> </ul>	d from preliminary to produc	t.	
	<ul> <li>Various chang</li> </ul>	es to content.		
NXPS20H100C v.1	20120420	Preliminary data shee	t -	-

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### 9.1 Data sheet status

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 8 June 2012 Document identifier: NXPS20H100C